



## PATENT ABSTRACTS OF JAPAN

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H01L 29/792(21) Application number: **03325543**(22) Date of filing: **10.12.1991**(71) Applicant: **HITACHI LTD**(72) Inventor: **ABE YOSHIO  
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tive substrate of a card size.

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(57) Abstract:

**PURPOSE:** To obtain easily a thin, lightweight memory card having a large capacity by using a thin-film transistor formed on an insulative substrate for a memory circuit.

**CONSTITUTION:** A solid-state storage element is composed of an electronic circuit constructed of a thin-film transistor TFT 13, a ferroelectric capacitor 14, etc., formed on an insulative substrate and of a protective film 11 for protecting the circuit from external environment, sealing resin 12 and an oversheet 2. The circuit construction of a memory cell is made up of the thin-film transistor TFT 13 and the ferroelectric capacitor 14. Since polarization remains in a ferroelectric even when no voltage is impressed, it can keep a stored content without a power source. Since this solid-state storage element is light in weight and thin and necessitates no power source at the time of stoppage, it can be used as a memory card by forming it on the insula-

